

IN THE CLAIMS

Claims 1-22 are presented below:

Claims 1-10 (canceled).

11. (Currently Amended) A method of fabricating conducting through-connections between a front face and a rear face of a substrate, comprising:

hollowing into the rear face of the substrate a cavity that surrounds a stud of substrate material formed by the cavity that provides, ~~from the rear face side, cavities having a depth and a cross section which are defined so as to delimit, by these cavities, studs of defined cross-section configured to provide~~ for electrical conduction between the front and rear faces;

filling in the ~~cavities~~ cavity with a dielectric material to insulate the stud from a rest of the substrate and to integrate the stud with the substrate while allowing the stud to show through the rear face;

hollowing the front face of the substrate opposite each stud so as to make ~~each~~ the stud show through the front face thereby converting the ~~and thus convert each~~ stud into a conducting through-connection; and

physically forming points of contact ~~opposite at each~~ end of the ~~face of each~~ stud showing through the substrate by depositing a conducting material, insulated from the substrate, on each of these ends ~~faces~~.

12. (Currently Amended): The method of fabricating conducting through-connections between the front face and the rear face of a substrate as claimed in claim 11, wherein the filling of the ~~eavities~~ cavity comprises:

depositing the dielectric material in the ~~eavities~~ cavity; and

removing, from a surface of the substrate, overflows of the deposit of dielectric material by thinning the rear face of the substrate until the ~~studs-are~~ stud is uncovered.

13. (Currently Amended) The method of fabricating conducting through-connections between the front face and the rear face of a substrate as claimed in claim 11, further comprising, after ~~delimiting the studs~~ forming the stud and before filling in the ~~eavities~~ cavity:

metallizing the ~~studs~~ stud by depositing a conducting layer on the ~~studs~~ stud.

14. (Currently Amended) The method of fabricating conducting through-connections between the front face and the rear face of a substrate as claimed in claim 13, wherein the filling-in of the ~~eavities~~ cavity comprises:

depositing the dielectric material in the ~~eavities~~ cavity;

removing, from a surface of the substrate, overflows of the deposit of the dielectric material by thinning the rear face of the substrate until the ~~studs-are~~ stud is uncovered; and

removing the conducting layer from the surface of the substrate, by thinning of the metallized faces of the substrate.

15. (Currently Amended) The method of fabricating conducting through-connections between the front face and the rear face of a substrate as claimed in claim 11, further comprising:

thinning the substrate until the dielectric material contained in the ~~eavities~~ cavity is uncovered so as to make the ~~studs~~ stud show through on the front face of the substrate.

16. (Currently Amended) The method of fabricating conducting through-connections between the front face and the rear face of a substrate as claimed in claim 11, further comprising:

hollowing the front face of the substrate opposite ~~each~~ the stud until the dielectric material contained in the ~~eavities~~ cavity is reached, so as to make the ~~studs~~ stud show through on the front face of the substrate.

17. (Currently Amended) The method of fabricating conducting through-connections between the front face and the rear face of a substrate as claimed in claim 11, wherein the physical formation of the points of contact comprises:

depositing an insulating layer on a same side as the faces of the ~~studs~~ stud showing through;

opening up a contact region opposite each face of the ~~studs~~ stud showing through by masking and etching of the insulating layer;

depositing a conducting layer on the same side as the faces of the ~~studs~~ stud showing through; and

cutting out the points of contact by masking and etching of the conducting layer.

18. (Original) The method of fabricating conducting through-connections between the front face and the rear face of a substrate as claimed in claim 11, wherein the dielectric filling material is glass.

19. (Currently Amended) A substrate of silicon equipped with a conducting through-connection ~~through-connections~~ between ~~its~~ a front face and ~~its~~ a rear face of the substrate, wherein;

the conducting through-connection comprises a ~~through-connections are silicon studs~~ extending stud of the substrate of silicon that extends over an entire height of the substrate and ~~are~~ is surrounded by a dielectric material which delimits the ~~studs~~ stud and keeps the ~~studs~~ stud integral with the substrate,

the ~~studs~~ stud showing through on the front and rear faces of the substrate, and

points of contact being formed opposite each face showing through of ~~each~~ the stud by a conducting material insulated from the substrate.

20. (Currently Amended) The substrate as claimed in claim 19, wherein the silicon ~~studs are~~ stud is coated substantially over ~~their~~ its entire height by a conducting metallization ~~itself that is~~ surrounded by the dielectric material.

21. (New) The method of fabricating conducting through connections between a front face and rear face of a substrate as claimed in Claim 11, wherein said hollowing into the substrate, said filling in the cavity, said hollowing the front face of the substrate, and said physically forming steps are performed at a plurality of areas of the substrate in order to form a plurality of conducting-through connections.

22. (New) The substrate as claimed in Claim 19, wherein said substrate comprises a plurality of said through-connections.